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LED1050-66-60

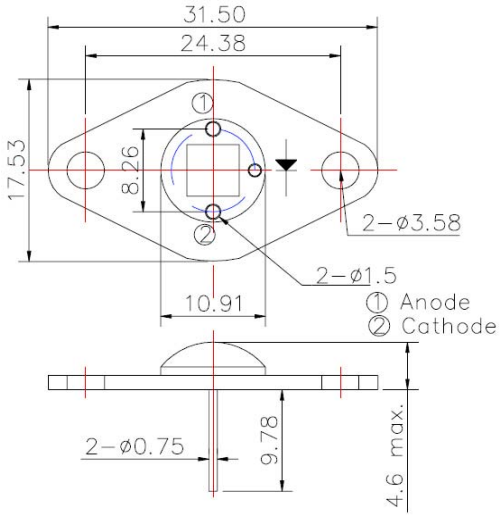
TECHNICAL DATA

High Power LED Array, 60 chips GaAs

LED1050-66-60 is a wide viewing and extremely high output power illuminator assembled with a total of 60 high efficiency GaAs diode chips, mounted on a metal stem TO-66 with AIN ceramics and covered with double coated clear silicone and epoxy resin.
These devices are designed for high current operation with proper heat sinking to improver thermal conductive efficiency.

Specifications

- Structure: GaAs, 60 LED chips
- Peak Wavelength: typ. 1050 nm
- Optical Output Power: typ. 120 mW
- Package: TO-66 stem with AIN,
  clear silicone and epoxy resin



(Unit: mm)

Absolute Maximum Ratings (T_C=25°C)

Item	Symbol	Value	Unit
Power Dissipation	P_D	6.0	W
Forward Current	I_F	800	mA
Reverse Voltage	V_R	30	V
Operating Temperature	T_{opr}	-30 … +80	°C
Storage Temperature	T_{stg}	-30 … +110	°C
Soldering Temperature *	T_{sol}	265	°C

* must be completed within 3 seconds

Electro-Optical Characteristics

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Total Radiated Power	P_O	I_F = 600 mA	-	120	-	mW
Forward Voltage	V_F	I_F = 600 mA	-	7.0	-	V
Reverse Voltage	V_R	I_R = 10 µA	30	-	-	V
Peak Wavelength	λ_P	I_F = 600 mA	1000	1050	1100	nm
Half Width	$\Delta\lambda$	I_F = 600 mA	-	55	-	nm
Viewing Half Angle	$\Theta_{1/2}$	I_F = 600 mA	-	±60	-	deg.
Rise Time	t_f	I_F = 600 mA	-	15	-	ns
Fall Time	t_f	I_F = 600 mA	-	10	-	ns

Heat Sink is required, thermal resistance <8K/W

Notes

- This high power LED must be cooled!
- Do not view directly into the emitting area of the LED during operation!
- The above specifications are for reference purpose only and subjected to change without prior notice.